



# PSMN1R9-80SSE

N-channel 80 V, 1.9 mOhm MOSFET with enhanced SOA in LFPK88

16 December 2022

Product data sheet

## 1. General description

N-channel enhancement mode MOSFET in a LFPK88 package qualified to 175 °C. Part of Nexperia's "ASFETs for hotswap" portfolio, the PSMN1R9-80SSE delivers very low  $R_{DS(on)}$  and a very strong linear-mode (SOA) performance in a high-reliability copper-clip LFPK88 package.

PSMN1R9-80SSE complements the latest "hot-swap" controllers – robust enough to withstand substantial inrush currents during turn-on, low  $R_{DS(on)}$  to minimize  $I^2R$  losses and deliver optimum efficiency when turned fully ON.

## 2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Low  $R_{DS(on)}$  for low  $I^2R$  conduction losses
- LFPK88 package for applications that demand the highest performance and reliability

## 3. Applications

- Hot swap
- Load switch
- Soft start
- E-fuse
- Telecommunication and computing systems based on a 48 V backplane/supply rail

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>		-	-	286	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>		-	-	340	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>		-	1.6	1.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; <a href="#">Fig. 13</a>		-	2.6	3	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		7	23	53	nC
Q <sub>G(tot)</sub>	total gate charge			77	155	232	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 90 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(i)nit</sub> = 25 °C; unclamped; t <sub>p</sub> = 179 μs; <a href="#">Fig. 4</a>	<a href="#">[1]</a>	-	-	840	mJ

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 40\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 18</a>	[2]	-	60	-	nC

[1] Protected by 100% test

[2] includes capacitive recovery

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<p>LFPAK88 (SOT1235)</p>	
2	S	source		
3	S	source		
4	S	source		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R9-80SSE	LFPAK88	plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body	SOT1235

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R9-80SSE	X1E9S80S

## 8. Limiting values

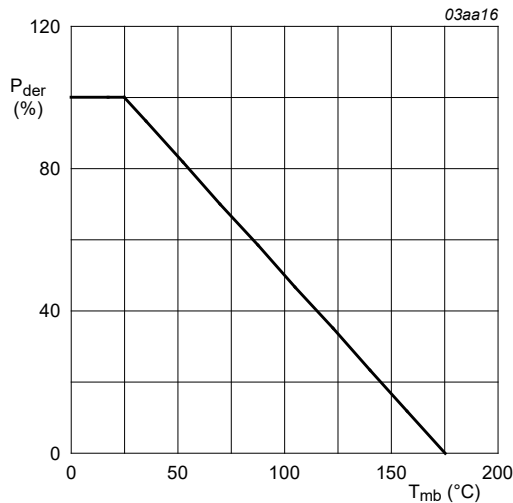
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$		-	80	V
$V_{DGR}$	drain-gate voltage	$25\text{ }^\circ\text{C} \leq T_j \leq 175\text{ }^\circ\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$		-	80	V
$V_{GS}$	gate-source voltage			-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>		-	340	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>		-	286	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>		-	202	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>		-	1142	A
$T_{stg}$	storage temperature			-55	175	$^\circ\text{C}$

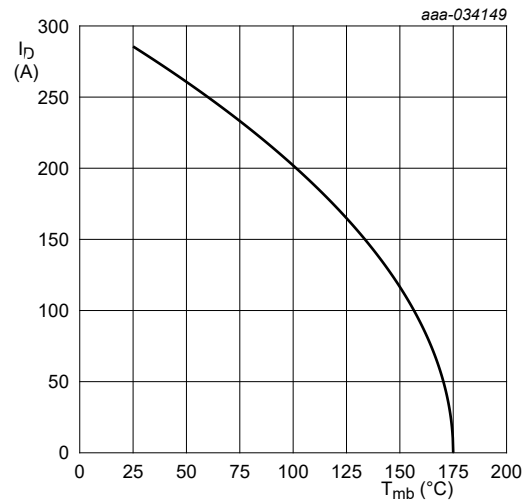
Symbol	Parameter	Conditions		Min	Max	Unit
$T_j$	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$		-	286	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$		-	1142	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 90\text{ A}$ ; $V_{sup} \leq 80\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; $t_p = 179\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a>	[1]	-	840	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 80\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $R_{GS} = 50\text{ }\Omega$ ; <a href="#">Fig. 4</a>	[1]	-	90	A

[1] Protected by 100% test



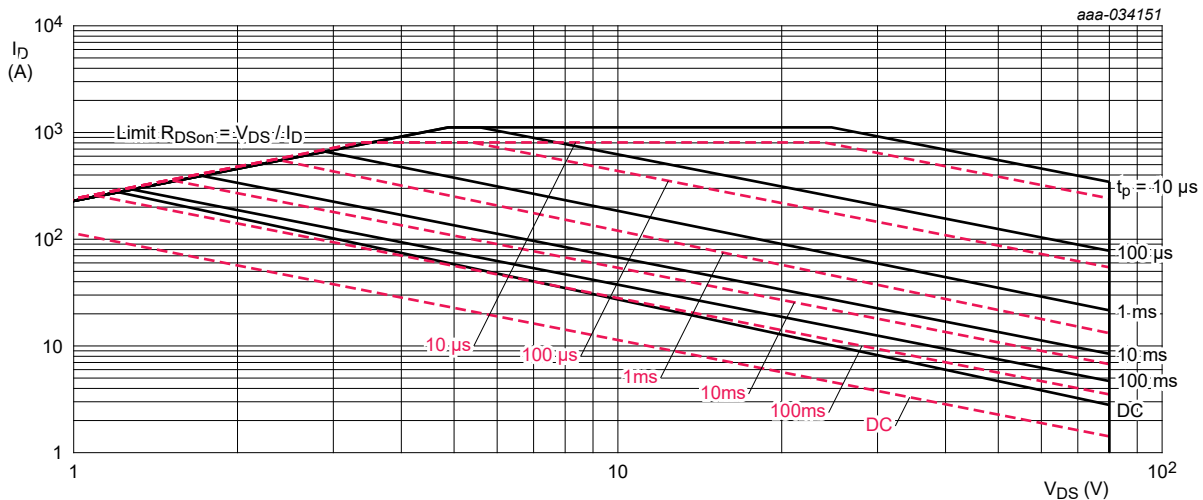
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

**Fig. 1.** Normalized total power dissipation as a function of mounting base temperature



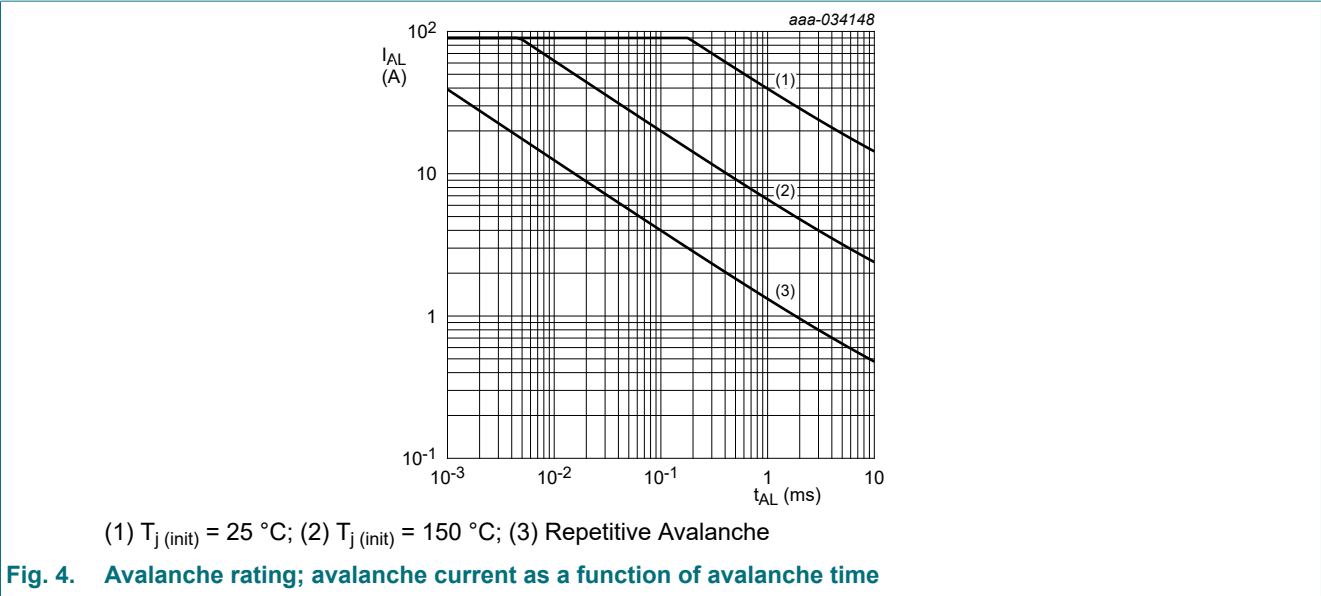
$V_{GS} \geq 10\text{ V}$

**Fig. 2.** Continuous drain current as a function of mounting base temperature



$T_{mb} = 25\text{ °C}$ ;  $I_{DM}$  is a single pulse

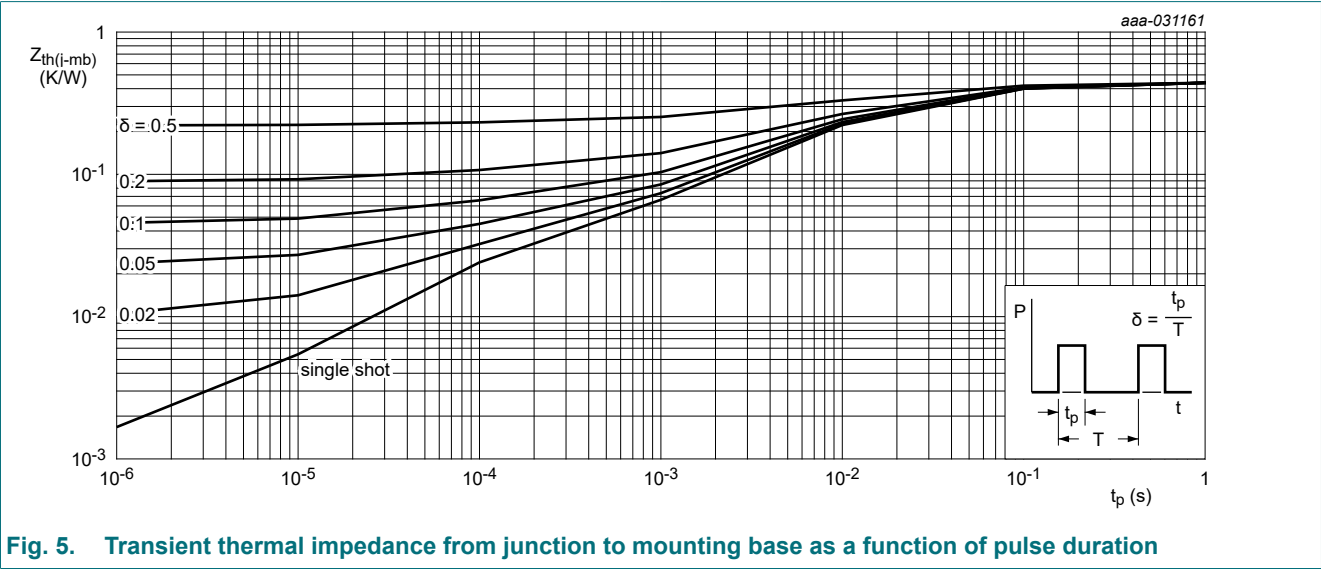
**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage

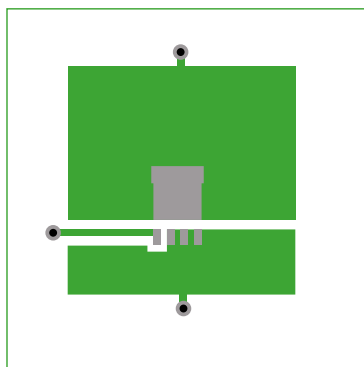


9. Thermal characteristics

Table 6. Thermal characteristics

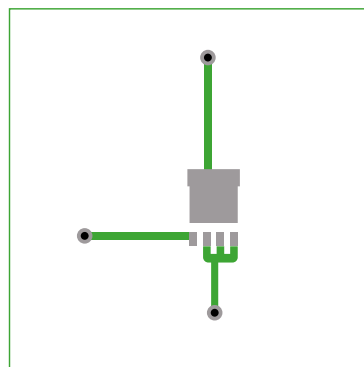
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.2	0.44	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 6	-	35	-	K/W
		Fig. 7	-	70	-	K/W





Copper square 25.4 mm x 25.4 mm; 70 μm thick on FR4 board

**Fig. 6. PCB layout for resistance from junction to ambient**



70 μm thick copper on FR4 board

**Fig. 7. PCB layout with minimum footprint for thermal resistance from junction to ambient**

## 10. Characteristics

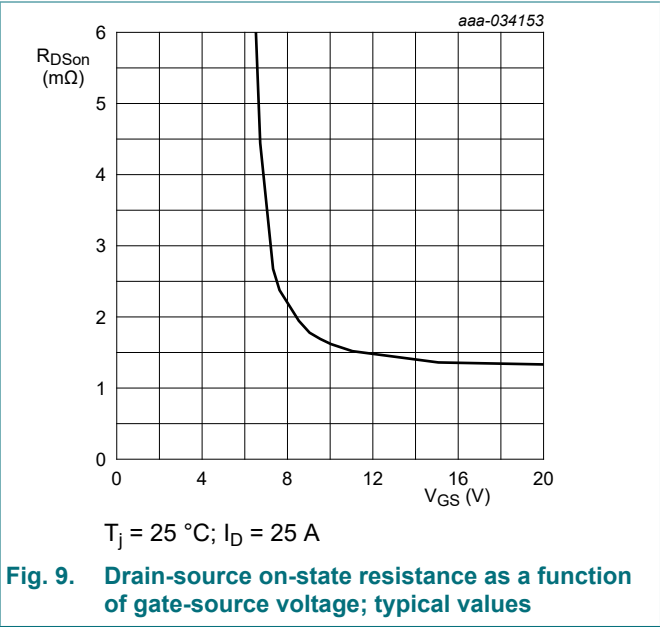
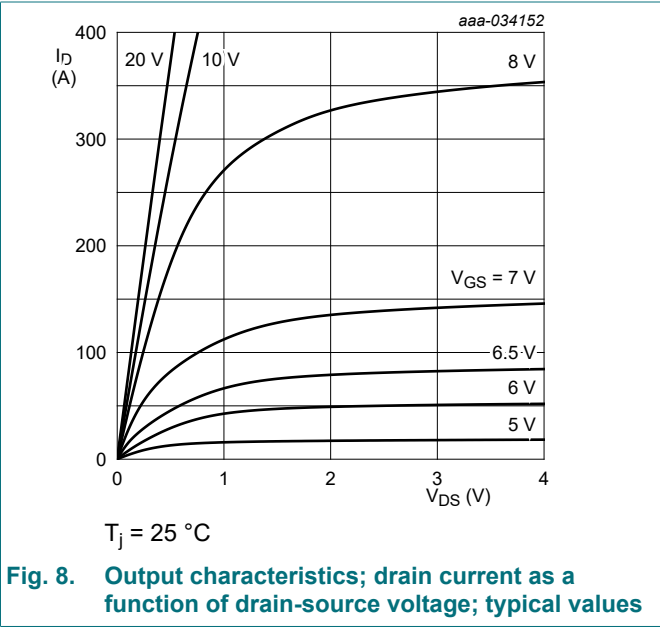
**Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^\circ C$	80	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^\circ C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 ^\circ C; \text{Fig. 11}$	2	2.6	3.6	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 ^\circ C$	-	1.6	-	V
		$I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 ^\circ C$	-	3	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 ^\circ C \leq T_j \leq 150 ^\circ C$	-	-6.4	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 ^\circ C$	-	0.02	1	μA
		$V_{DS} = 16 V; V_{GS} = 0 V; T_j = 125 ^\circ C$	-	3	100	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 ^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 ^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_j = 25 ^\circ C; \text{Fig. 12}$	-	1.6	1.9	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 100 ^\circ C; \text{Fig. 13}$	-	2.6	3	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_j = 175 ^\circ C; \text{Fig. 13}$	-	-	4.2	mΩ
$R_G$	gate resistance	$f = 1 MHz; T_j = 25 ^\circ C$	0.8	1.6	3.2	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 40 V; V_{GS} = 10 V; T_j = 25 ^\circ C; \text{Fig. 14; Fig. 15}$	77	155	232	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 ^\circ C; \text{Fig. 14; Fig. 15}$	-	83	-	nC

N-channel 80 V, 1.9 mOhm MOSFET with enhanced SOA in LFPAK88

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		36	60	84	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge			-	34	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge			-	26	-	nC
Q <sub>GD</sub>	gate-drain charge			7	23	53	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>		-	5.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; f = 0.5 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>		7340	12235	17140	pF
C <sub>oss</sub>	output capacitance			1710	2843	4560	pF
C <sub>rss</sub>	reverse transfer capacitance			7	64	169	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 40 V; R <sub>L</sub> = 1.6 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C		-	46	-	ns
t <sub>r</sub>	rise time			-	42	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	79	-	ns
t <sub>f</sub>	fall time			-	46	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 17</a>		-	0.78	1	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 40 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 18</a>		-	54	-	ns
Q <sub>r</sub>	recovered charge		[1]	-	60	-	nC

[1] includes capacitive recovery



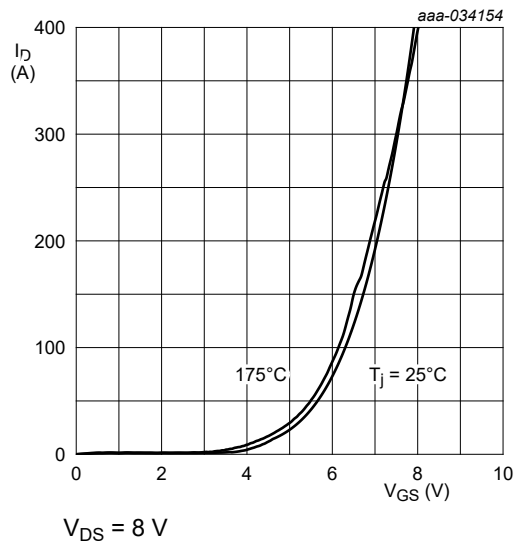


Fig. 10. Transfer characteristics; drain current as a function of gate-source voltage; typical values

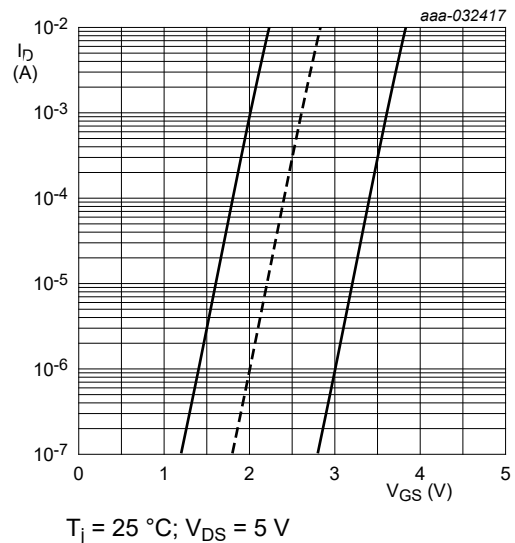


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

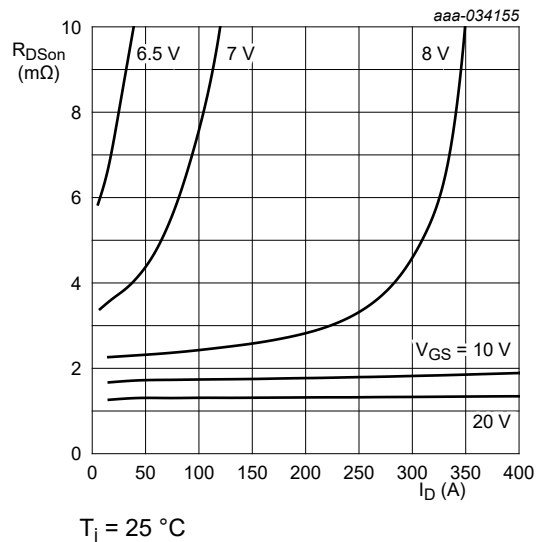


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

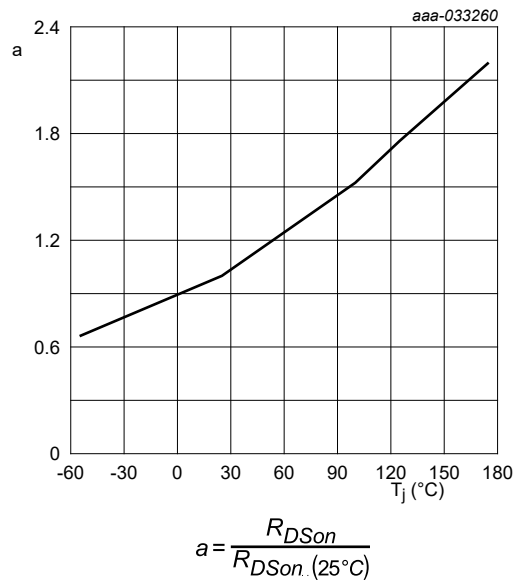


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

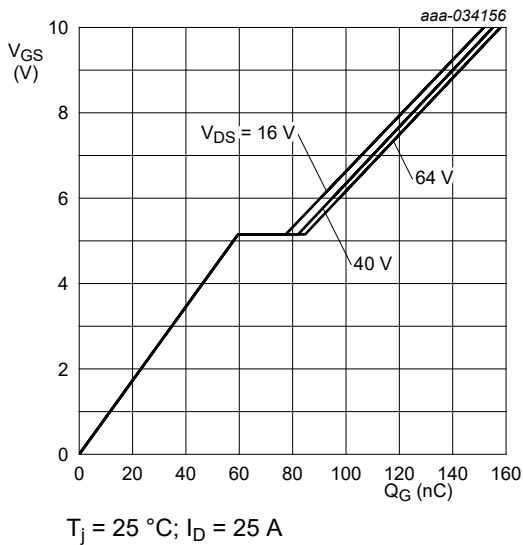


Fig. 14. Gate-source voltage as a function of gate charge; typical values

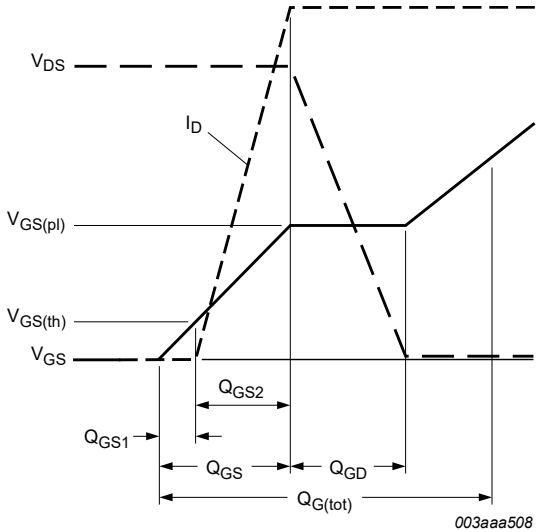


Fig. 15. Gate charge waveform definitions

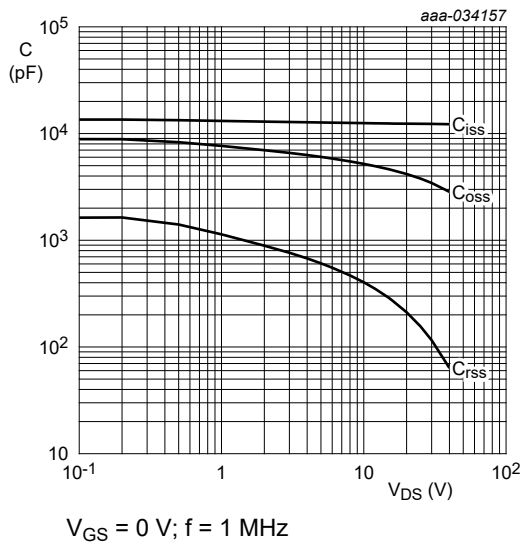


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

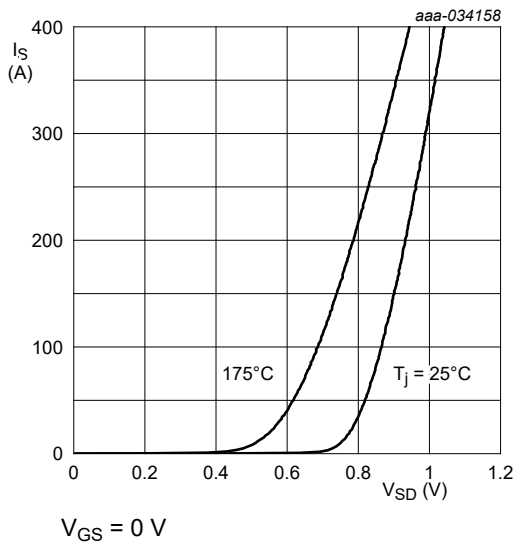


Fig. 17. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

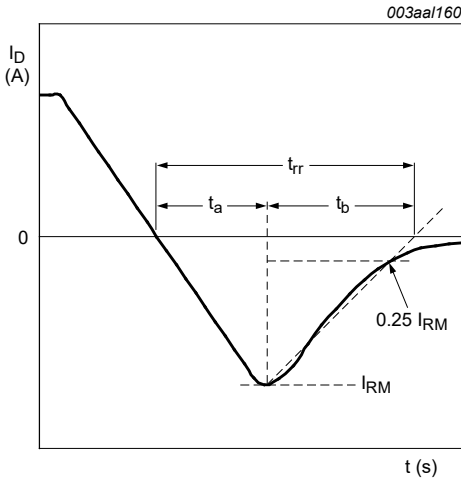


Fig. 18. Reverse recovery timing definition



11. Package outline

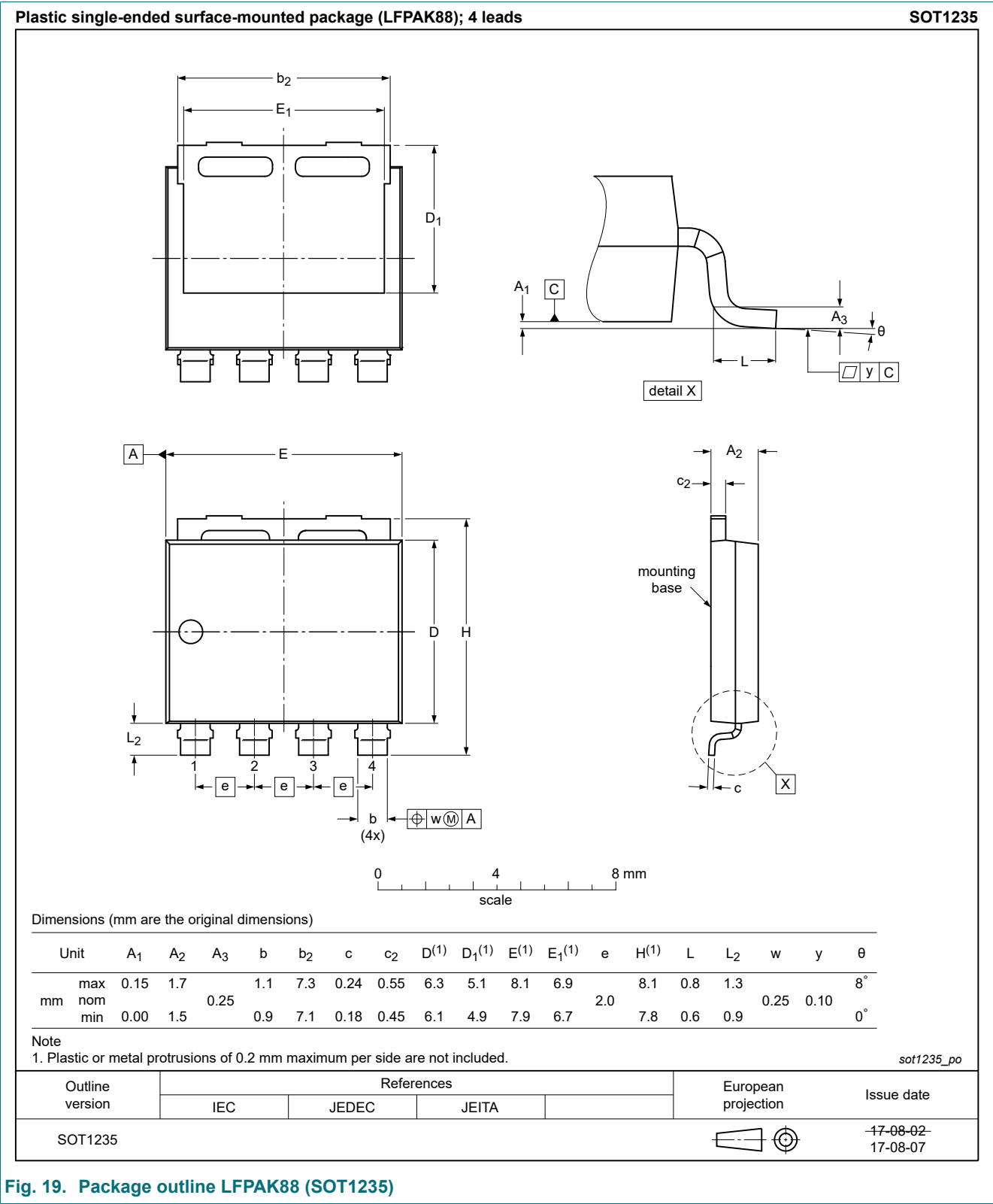
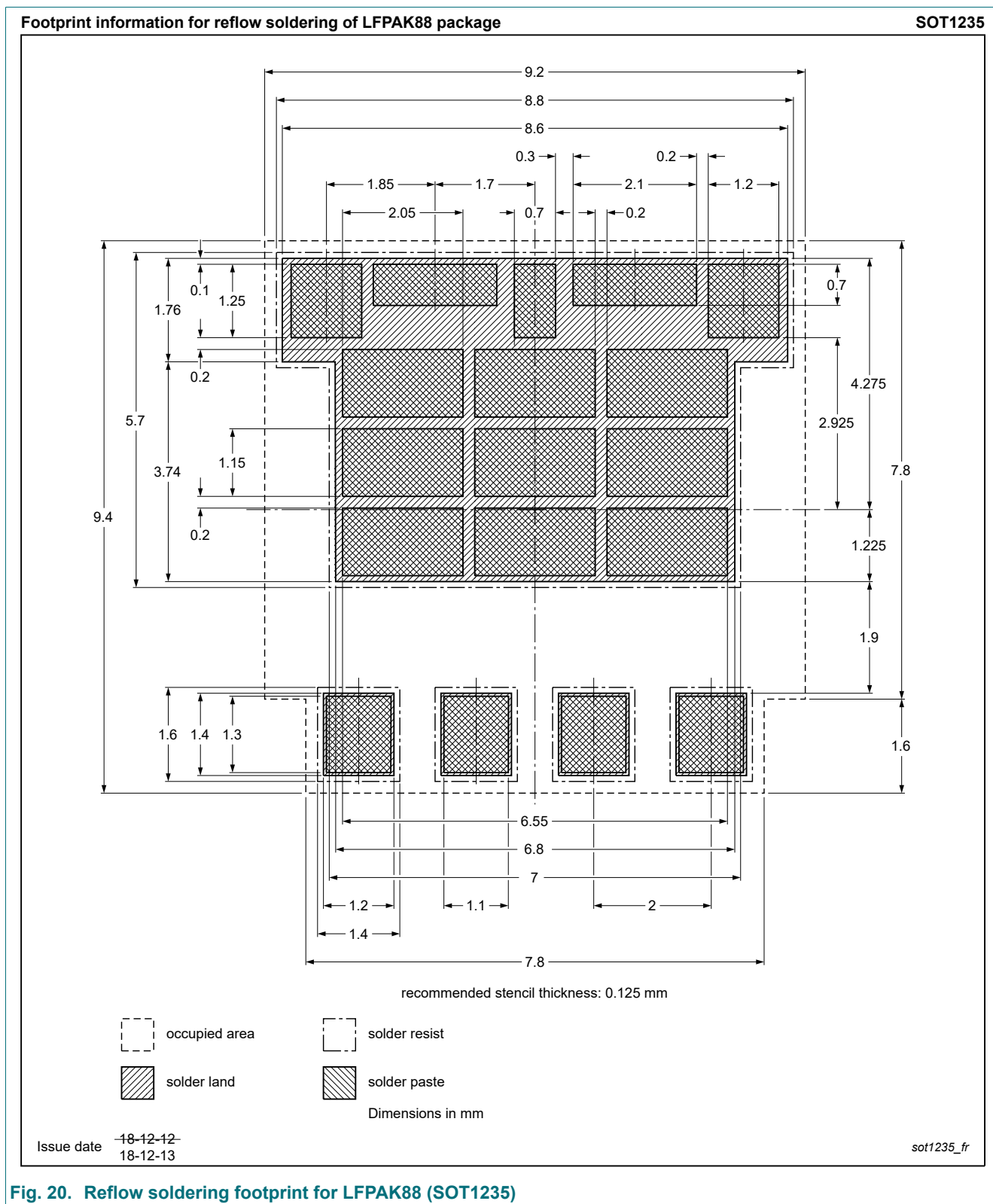


Fig. 19. Package outline LPAK88 (SOT1235)

## 12. Soldering



**Fig. 20. Reflow soldering footprint for LPAK88 (SOT1235)**

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Contents

1. General description..... 1

2. Features and benefits..... 1

3. Applications..... 1

4. Quick reference data..... 1

5. Pinning information.....2

6. Ordering information.....2

7. Marking.....2

8. Limiting values..... 2

9. Thermal characteristics..... 4

10. Characteristics..... 5

11. Package outline..... 9

12. Soldering..... 10

13. Legal information.....11

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